

# PEMB30; PUMB30

PNP/PNP double resistor-equipped transistors;  
R1 = 2.2 k $\Omega$ , R2 = open

Rev. 02 — 2 September 2009

Product data sheet

## 1. Product profile

### 1.1 General description

PNP/PNP double Resistor-Equipped Transistors (RET) in Surface-Mounted Device (SMD) plastic packages

Table 1. Product overview

Type number	Package		NPN/PNP complement	NPN/PNP complement
	NXP	JEITA		
PEMB30	SOT666	-	PEMD30	PEMH30
PUMB30	SOT363	SC-88	PUMD30	PUMH30

### 1.2 Features

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs

### 1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Cost-saving alternative for BC857BS and BC857BV

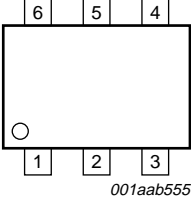
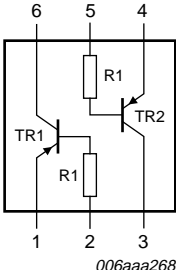
### 1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Per transistor						
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	-50	V
I <sub>O</sub>	output current		-	-	-100	mA
R1	bias resistor 1 (input)		1.54	2.2	2.86	k $\Omega$

2. Pinning information

Table 3. Pinning

Pin	Description	Simplified outline	Symbol
1	GND (emitter) TR1	 001aab555	 006aaa268
2	input (base) TR1		
3	output (collector) TR2		
4	GND (emitter) TR2		
5	input (base) TR2		
6	output (collector) TR1		

3. Ordering information

Table 4. Ordering information

Type number	Package		
	Name	Description	Version
PEMB30	-	plastic surface-mounted package; 6 leads	SOT666
PUMB30	SC-88	plastic surface-mounted package; 6 leads	SOT363

4. Marking

Table 5. Marking codes

Type number	Marking code <sup>[1]</sup>
PEMB30	2T
PUMB30	*B2

[1] \* = -: made in Hong Kong  
\* = p: made in Hong Kong  
\* = t: made in Malaysia  
\* = W: made in China

## 5. Limiting values

**Table 6. Limiting values**

*In accordance with the Absolute Maximum Rating System (IEC 60134).*

Symbol	Parameter	Conditions	Min	Max	Unit
<b>Per transistor</b>					
V <sub>CBO</sub>	collector-base voltage	open emitter	-	-50	V
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-50	V
V <sub>EBO</sub>	emitter-base voltage	open collector	-	-5	V
I <sub>O</sub>	output current		-	-100	mA
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms	-	-100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C			
	SOT363		[1]	200	mW
	SOT666		[1][2]	200	mW
<b>Per device</b>					
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C			
	SOT363		[1]	300	mW
	SOT666		[1][2]	300	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
T <sub>j</sub>	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

## 6. Thermal characteristics

**Table 7. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Per transistor</b>						
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air				
	SOT363		[1]	-	625	K/W
	SOT666		[1][2]	-	625	K/W
<b>Per device</b>						
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air				
	SOT363		[1]	-	416	K/W
	SOT666		[1][2]	-	416	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

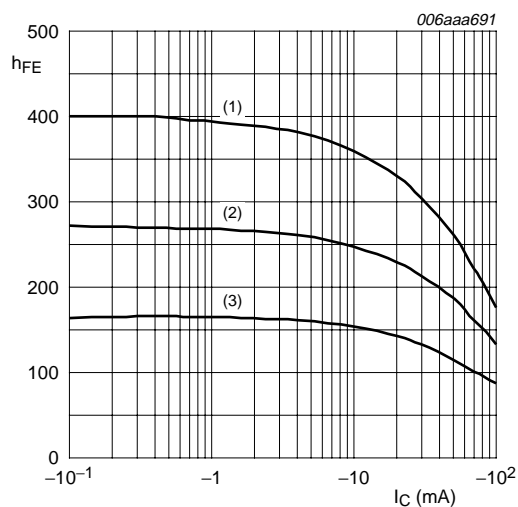
[2] Reflow soldering is the only recommended soldering method.

## 7. Characteristics

**Table 8. Characteristics**

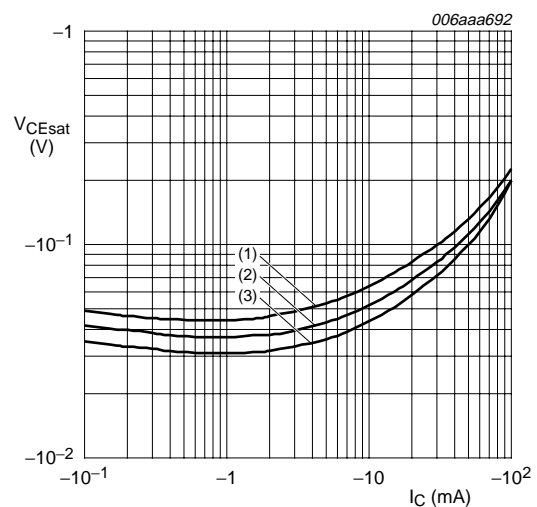
$T_{amb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Per transistor</b>						
$I_{CBO}$	collector-base cut-off current	$V_{CB} = -50\text{ V}; I_E = 0\text{ A}$	-	-	-100	nA
$I_{CEO}$	collector-emitter cut-off current	$V_{CE} = -30\text{ V}; I_B = 0\text{ A}$	-	-	-1	μA
		$V_{CE} = -30\text{ V}; I_B = 0\text{ A}; T_j = 150\text{ }^{\circ}\text{C}$	-	-	-50	μA
$I_{EBO}$	emitter-base cut-off current	$V_{EB} = -5\text{ V}; I_C = 0\text{ A}$	-	-	-100	nA
$h_{FE}$	DC current gain	$V_{CE} = -5\text{ V}; I_C = -20\text{ mA}$	30	-	-	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = -10\text{ mA}; I_B = -0.5\text{ mA}$	-	-	-150	mV
R1	bias resistor 1 (input)		1.54	2.2	2.86	kΩ
$C_c$	collector capacitance	$V_{CB} = -10\text{ V}; I_E = i_e = 0\text{ A}; f = 1\text{ MHz}$	-	-	3	pF



- $V_{CE} = -5\text{ V}$
- (1)  $T_{amb} = 100\text{ }^{\circ}\text{C}$
  - (2)  $T_{amb} = 25\text{ }^{\circ}\text{C}$
  - (3)  $T_{amb} = -40\text{ }^{\circ}\text{C}$

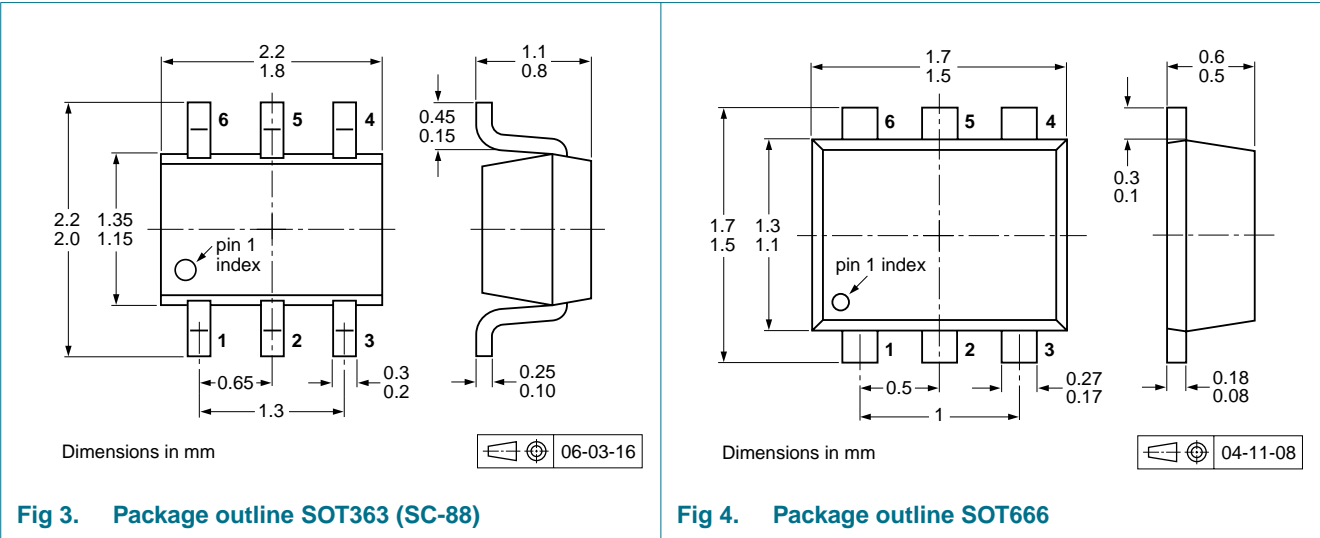
**Fig 1. DC current gain as a function of collector current; typical values**



- $I_C/I_B = 20$
- (1)  $T_{amb} = 100\text{ }^{\circ}\text{C}$
  - (2)  $T_{amb} = 25\text{ }^{\circ}\text{C}$
  - (3)  $T_{amb} = -40\text{ }^{\circ}\text{C}$

**Fig 2. Collector-emitter saturation voltage as a function of collector current; typical values**

8. Package outline



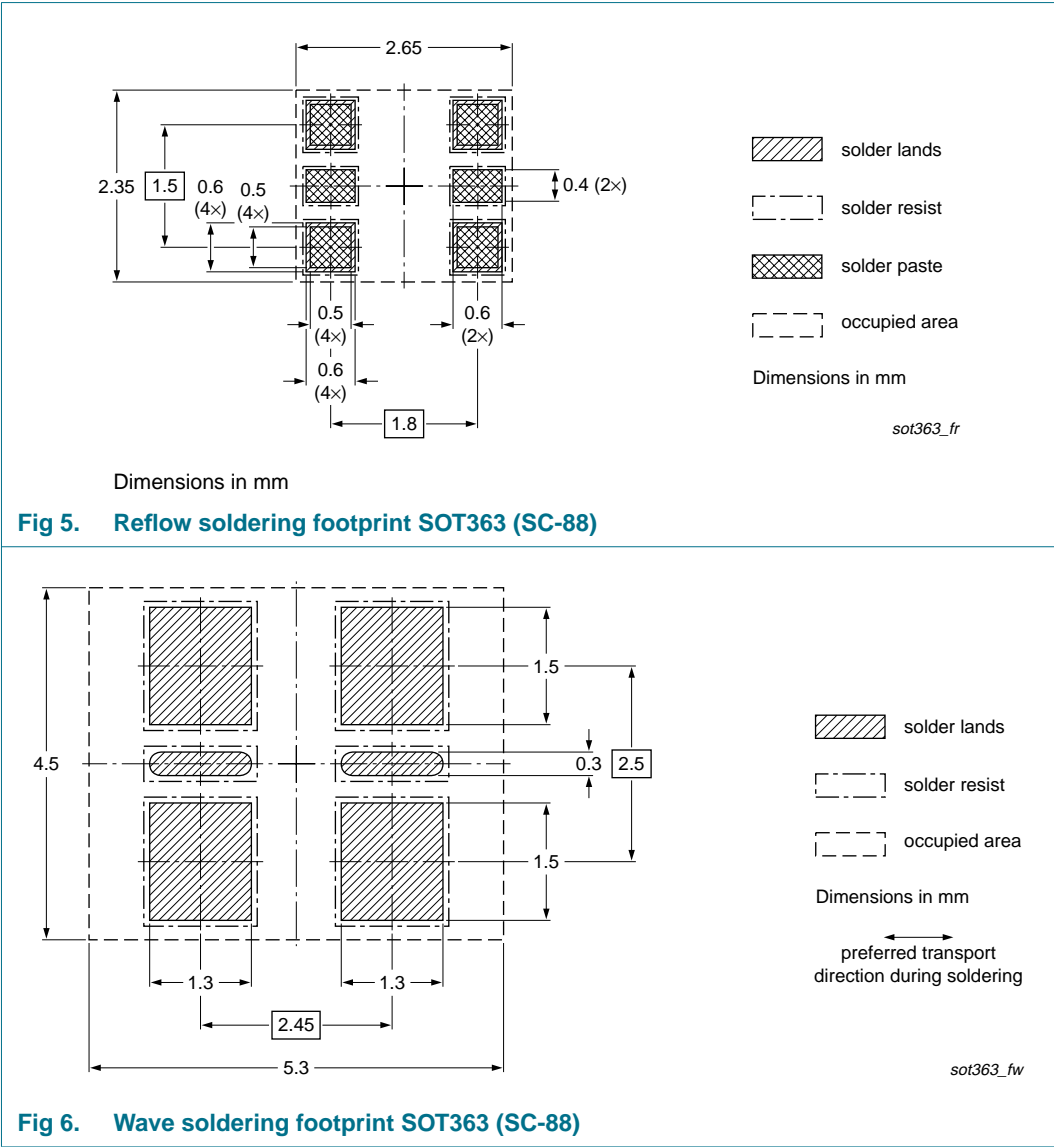
9. Packing information

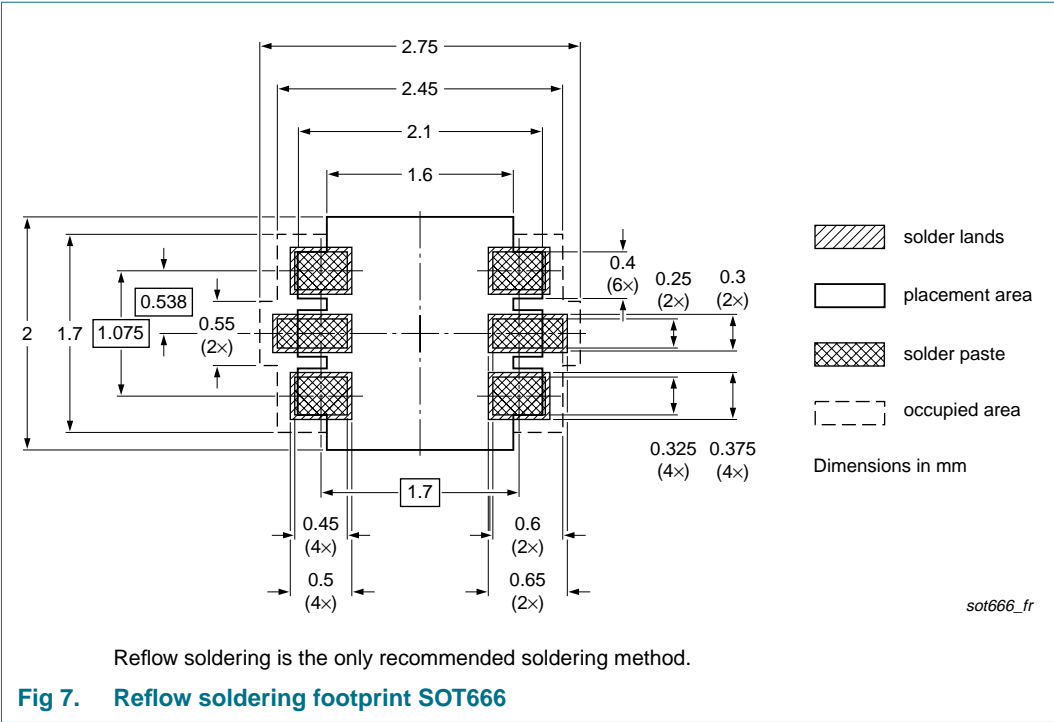
Table 9. Packing methods  
The indicated -xxx are the last three digits of the 12NC ordering code.<sup>[1]</sup>

Type number	Package	Description	Packing quantity			
			3000	4000	8000	10000
PEMB30	SOT666	2 mm pitch, 8 mm tape and reel	-	-	-315	-
		4 mm pitch, 8 mm tape and reel	-	-115	-	-
PUMB30	SOT363	4 mm pitch, 8 mm tape and reel; T1 <sup>[2]</sup>	-115	-	-	-135
		4 mm pitch, 8 mm tape and reel; T2 <sup>[3]</sup>	-125	-	-	-165

[1] For further information and the availability of packing methods, see [Section 13](#).  
[2] T1: normal taping  
[3] T2: reverse taping

10. Soldering





## 11. Revision history

**Table 10. Revision history**

Document ID	Release date	Data sheet status	Change notice	Supersedes
PEMB30_PUMB30_2	20090902	Product data sheet	-	PEMB30_PUMB30_1
Modifications:	<ul style="list-style-type: none"><li>• This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content.</li><li>• <a href="#">Figure 3 "Package outline SOT363 (SC-88)"</a>: updated</li><li>• <a href="#">Figure 5 "Reflow soldering footprint SOT363 (SC-88)"</a>: updated</li><li>• <a href="#">Figure 6 "Wave soldering footprint SOT363 (SC-88)"</a>: updated</li><li>• <a href="#">Figure 7 "Reflow soldering footprint SOT666"</a>: updated</li></ul>			
PEMB30_PUMB30_1	20060331	Product data sheet	-	-



## 12. Legal information

### 12.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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